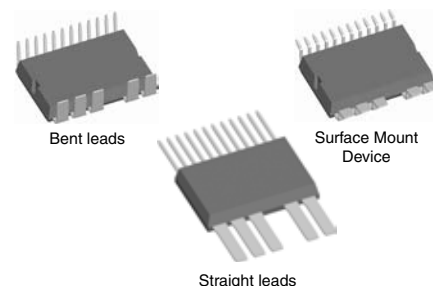
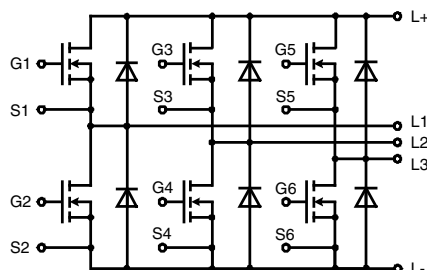


Three phase full Bridge with Trench MOSFETs in DCB isolated high current package

$$\begin{aligned}
V_{DSS} &= 40 \text{ V} \\
I_{D25} &= 180 \text{ A} \\
R_{DSon \text{ typ.}} &= 2.0 \text{ m}\Omega
\end{aligned}$$

Preliminary data



MOSFETs			
Symbol	Conditions	Maximum Ratings	
V_{DSS}	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	40	V
V_{GS}		± 20	V
I_{D25}	$T_C = 25^{\circ}\text{C}$	180	A
I_{D90}	$T_C = 90^{\circ}\text{C}$	138	A
I_{F25}	$T_C = 25^{\circ}\text{C (diode)}$	115	A
I_{F90}	$T_C = 90^{\circ}\text{C (diode)}$	75	A

Applications

AC drives

- in automobiles
 - electric power steering
 - starter generator
- in industrial vehicles
 - propulsion drives
 - fork lift drives
- in battery supplied equipment

Features

- MOSFETs in trench technology:
 - low R_{DSon}
 - optimized intrinsic reverse diode
- package:
 - high level of integration
 - high current capability 300 A max.
 - aux. terminals for MOSFET control
 - terminals for soldering or welding connections
 - isolated DCB ceramic base plate with optimized heat transfer
- Space and weight savings

Package options

- 3 lead forms available
 - straight leads (SL)
 - SMD lead version (SMD)
 - bent leads (BL)

Symbol	Conditions	Characteristic Values			
		(T _{VJ} = 25°C, unless otherwise specified)			
		min.	typ.	max.	
R_{DSon}	on chip level at $V_{GS} = 10 \text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$		2.0	mΩ
		$T_{VJ} = 125^{\circ}\text{C}$		3.2	mΩ
$V_{GS(th)}$	$V_{DS} = 20 \text{ V}; I_D = 1 \text{ mA}$	2		4	V
I_{DSS}	$V_{DS} = V_{DSS}; V_{GS} = 0 \text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$		0.1	μA
		$T_{VJ} = 125^{\circ}\text{C}$			mA
I_{GSS}	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$			0.2	μA
Q_g	$V_{GS} = 10 \text{ V}; V_{DS} = 14 \text{ V}; I_D = 25 \text{ A}$		94		nC
Q_{gs}			18		nC
Q_{gd}			29		nC
$t_{d(on)}$	$V_{GS} = 10 \text{ V}; V_{DS} = 30 \text{ V}$ $I_D = 25 \text{ A}; R_G = 10 \Omega$ inductive load		40		ns
t_r			85		ns
$t_{d(off)}$			140		ns
t_f			90		ns
E_{on}			tbd		mJ
E_{off}			tbd		mJ
E_{recoff}			tbd		mJ
R_{thJC}	with heat transfer paste (IXYS test setup)		1.3	1.0	K/W
R_{thJH}				1.6	K/W

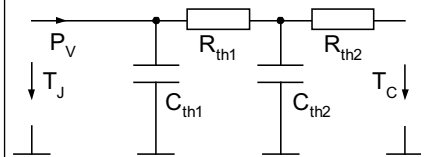
Source-Drain Diode

Symbol	Conditions	Characteristic Values			
		(T _J = 25°C, unless otherwise specified)			
		min.	typ.	max.	
V _{SD}	(diode) I _F = 110 A; V _{GS} = 0 V		1.0	1.6	V
t _{rr}	I _F = 20 A; -di _F /dt = 100 A/μs; V _R = 20 V		70		ns
Q _{RM}			tbd		μC
I _{RM}			tbd		A

Component

Symbol	Conditions	Maximum Ratings	
I _{RMS}	per pin in main current paths (P+, N-, L1, L2, L3) may be additionally limited by external connections	300	A
T _{VJ}		-55...+175	°C
T _{stg}		-55...+125	°C
V _{ISOL}	I _{ISOL} ≤ 1 mA, 50/60 Hz, f = 1 minute	1000	V~
F _C	mounting force with clip	50 - 250	N

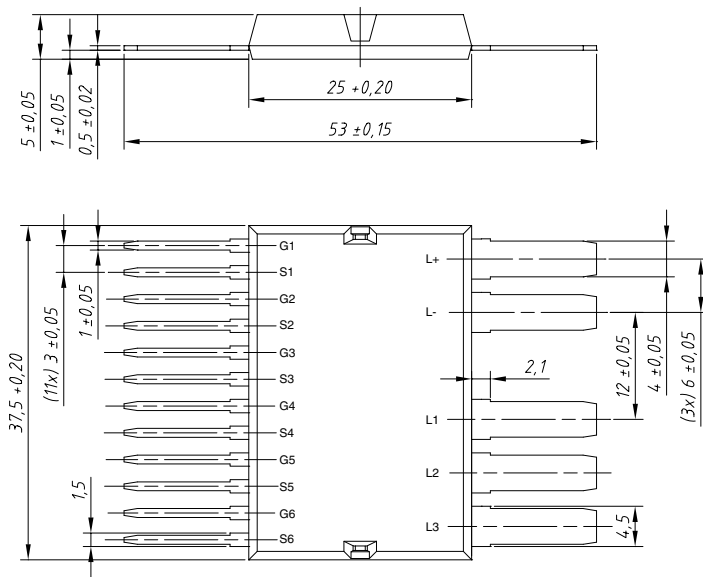
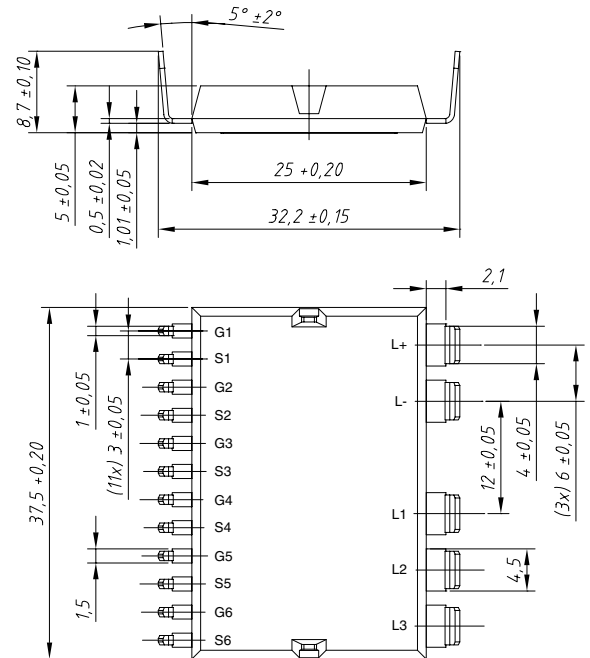
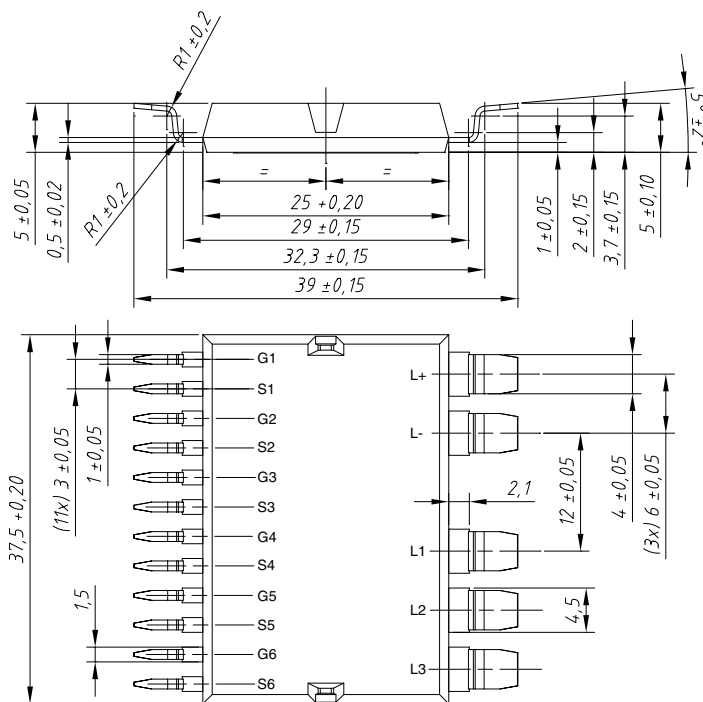
Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
R _{pin to chip}	with heatsink compound		0.6		mΩ
C _P	coupling capacity between shorted pins and mounting tab in the case		160		pF
Weight	typ.		25		g

Equivalent Circuits for Simulation
Thermal Response


junction - case (typ.)

$$C_{th1} = \text{tbd J/K}; R_{th1} = \text{tbd K/W}$$

$$C_{th2} = \text{tbd J/K}; R_{th2} = \text{tbd K/W}$$

Straight Leads GWM 220-003P3-SL

Bent Leads GWM 220-003P3-BL

Surface Mount Device GWM 220-003P3-SMD


Leads	Ordering	Part Name & Packing Unit Marking	Part Marking	Delivering Mode	Base Qty.	Ordering Code
Straight	Standard	GWM 220-004P3 - SL	GWM 220-004P3	Blister	36	503 169
SMD	Standard	GWM 220-004P3 - SMD	GWM 220-004P3	Blister	36	503 176
Bent	Standard	GWM 220-004P3 - BL	GWM 220-004P3	Blister	36	contact factory